Magnus BorgstrÃ¶m

List of Publications by Year
in descending order

Version: 2024-02-01

195 papers	9,082 citations	53660 45 h-index	43802 91 g-index
197 all docs	197 docs citations	197 times ranked	7011 citing authors

#	Article	IF	Citations
1	Realization of axially defined GaInP/InP/InAsP triple-junction photovoltaic nanowires for high-performance solar cells. Materials Today Energy, 2022, 27, 101050.	2.5	11
2	Development and characterization of photovoltaic tandem-junction nanowires using electron-beam-induced current measurements. Nano Research, 2022, 15, 8510-8515.	5.8	4
3	Compositional analysis of oxide-embedded IIIâ€“V nanostructures. Nanotechnology, 2022, 33, 375705.	1.3	0
4	Comparison of Triethylgallium and Trimethylgallium Precursors for GaInP Nanowire Growth. Physica Status Solidi (B): Basic Research, 2021, 258, 2000400.	0.7	3
5	Gain and bandwidth of InP nanowire array photodetectors with embedded photogated InAsP quantum discs. Nanoscale, 2021, 13, 6227-6233.	2.8	6
6	Imaging the influence of oxides on the electrostatic potential of photovoltaic InP nanowires. Nano Research, 2021, 14, 4087-4092.	5.8	5
7	Semiconductor nanowire array for transparent photovoltaic applications. Applied Physics Letters, 2021, 118, 191107.	1.5	9
8	Design study of a nanowire three-terminal heterojunction bipolar transistor solar cell. , 2021, , .		1
9	In situ passivation of Ga_xIn_(1â^'x)P nanowires using radial Al_yIn_(1â^'y)P shells grown by MOVPE. Nanotechnology, 2021, 32, 425705.	1.3	3
10	Wafer-Scale Synthesis and Optical Characterization of InP Nanowire Arrays for Solar Cells. Nano Letters, 2021, 21, 7347-7353.	4.5	7
11	Probing strain in wurtzite InP-InAs core-shell nanowires with Raman spectroscopy. Physical Review B, 2021, 104, .	1.1	2
12	Template-assisted vapourâ€“liquidâ€“solid growth of InP nanowires on (001) InP and Si substrates. Nanoscale, 2020, 12, 888-894.	2.8	7
13	Operando Surface Characterization of InP Nanowire pâ€“n Junctions. Nano Letters, 2020, 20, 887-895.	4.5	13
14	Implementing an Insect Brain Computational Circuit Using IIIâ€“V Nanowire Components in a Single Shared Waveguide Optical Network. ACS Photonics, 2020, 7, 2787-2798.	3.2	5
15	Ultrafast Optical Generation of Coherent Bright and Dark Surface Phonon Polaritons in Nanowires. ACS Photonics, 2020, 7, 1923-1931.	3.2	2
16	Light current-voltage measurements of single, as-grown, nanowire solar cells standing vertically on a substrate. Nano Energy, 2020, 78, 105191.	8.2	14
17	Photovoltaic nanowires affect human lung cell proliferation under illumination conditions. Nanoscale, 2020, 12, 14237-14244.	2.8	2
18	Optoelectronic III-V nanowire implementation of a neural network in a shared waveguide. , 2020, , .		0

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19	Self-Limiting Polymer Exposure for Vertical Processing of Semiconductor Nanowire-Based Flexible Electronics. ACS Applied Nano Materials, 2020, 3, 7743-7749.	2.4	9
20	Direct Three-Dimensional Imaging of an X-ray Nanofocus Using a Single 60 nm Diameter Nanowire Device. Nano Letters, 2020, 20, 8326-8331.	4.5	8
21	Hot-carrier separation in heterostructure nanowires observed by electron-beam induced current. Nanotechnology, 2020, 31, 394004.	1.3	10
22	High resolution strain mapping of a single axially heterostructured nanowire using scanning X-ray diffraction. Nano Research, 2020, 13, 2460-2468.	5.8	11
23	Unravelling processing issues of nanowire-based solar cell arrays by use of electron beam induced current measurements. Nano Energy, 2020, 71, 104575.	8.2	13
24	Embedded sacrificial AlAs segments in GaAs nanowires for substrate reuse. Nanotechnology, 2020, 31, 204002.	1.3	8
25	Nanowire Solar Cells: A New Radiation Hard PV Technology for Space Applications. IEEE Journal of Photovoltaics, 2020, 10, 502-507.	1.5	15
26	Development and Characterization of a bottom-up InP Nanowire Solar Cell with 16.7% Efficiency. , 2020, , .		6
27	Irradiation Experiments on High Efficiency Nanowire Solar Cells Including Tilted Incidence Angle. , 2020, , .		0
28	Effect of hydrogen chloride etching on carrier recombination processes of indium phosphide nanowires. Nanoscale, 2019, 11, 18550-18558.	2.8	13
29	Revealing misfit dislocations in InAs_xP_{1â^'x}-InP coreâ€“shell nanowires by x-ray diffraction. Nanotechnology, 2019, 30, 505703.	1.3	10
30	Combining Nanofocused X-Rays with Electrical Measurements at the NanoMAX Beamline. Crystals, 2019, 9, 432.	1.0	11
31	Radiation Tolerant Nanowire Array Solar Cells. ACS Nano, 2019, 13, 12860-12869.	7.3	27
32	Three-Dimensional Imaging of Beam-Induced Biasing of InP/GaInP Tunnel Diodes. Nano Letters, 2019, 19, 3490-3497.	4.5	4
33	Measurements of Strain and Bandgap of Coherently Epitaxially Grown Wurtzite InAsPâ€“InP Coreâ€“Shell Nanowires. Nano Letters, 2019, 19, 2674-2681.	4.5	16
34	Simultaneous Growth of Pure Wurtzite and Zinc Blende Nanowires. Nano Letters, 2019, 19, 2723-2730.	4.5	13
35	Culturing and patch clamping of Jurkat T cells and neurons on Al₂O₃ coated nanowire arrays of altered morphology. RSC Advances, 2019, 9, 11194-11201.	1.7	9
36	Coulomb blockade from the shell of an InP-InAs core-shell nanowire with a triangular cross section. Applied Physics Letters, 2019, 114, 053108.	1.5	12

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37	UV exposure: a novel processing method to fabricate nanowire solar cells. , 2019, , .		2
38	Nanoprobe-Enabled Electron Beam Induced Current Measurements on III-V Nanowire-Based Solar Cells. , 2019, , .		1
39	High Responsivity of InP/InAsP Nanowire Array Broadband Photodetectors Enhanced by Optical Gating. Nano Letters, 2019, 19, 8424-8430.	4.5	13
40	Nanowire photodetectors with embedded quantum heterostructures for infrared detection. Infrared Physics and Technology, 2019, 96, 209-212.	1.3	6
41	Nanoscale mapping of carrier collection in single nanowire solar cells using X-ray beam induced current. Journal of Synchrotron Radiation, 2019, 26, 102-108.	1.0	12
42	Towards Nanowire Tandem Junction Solar Cells on Silicon. IEEE Journal of Photovoltaics, 2018, 8, 733-740.	1.5	53
43	Intersubband Quantum Disc-in-Nanowire Photodetectors with Normal-Incidence Response in the Long-Wavelength Infrared. Nano Letters, 2018, 18, 365-372.	4.5	34
44	Self-assembled InN quantum dots on side facets of GaN nanowires. Journal of Applied Physics, 2018, 123, .	1.1	14
45	Understanding InP Nanowire Array Solar Cell Performance by Nanoprobe-Enabled Single Nanowire Measurements. Nano Letters, 2018, 18, 3038-3046.	4.5	69
46	Electrical and optical evaluation ofn-type doping in In_xGa_(1â^'x)P nanowires. Nanotechnology, 2018, 29, 255701.	1.3	7
47	InP/GaInP nanowire tunnel diodes. Nano Research, 2018, 11, 2523-2531.	5.8	26
48	Nanobeam X-ray Fluorescence Dopant Mapping Reveals Dynamics of in Situ Zn-Doping in Nanowires. Nano Letters, 2018, 18, 6461-6468.	4.5	19
49	Spectrally resolved x-ray beam induced current in a single InGaP nanowire. Nanotechnology, 2018, 29, 454001.	1.3	9
50	Growth kinetics of Ga _x In_(1â^'x)P nanowires using triethylgallium as Ga precursor. Nanotechnology, 2018, 29, 394001.	1.3	10
51	Solar Cell Nanowires as Approach for Single Cell Direct Activation. Biophysical Journal, 2018, 114, 669a.	0.2	0
52	Bias-dependent spectral tuning in InP nanowire-based photodetectors. Nanotechnology, 2017, 28, 114006.	1.3	10
53	Ground State Depletion Nanoscopy Resolves Semiconductor Nanowire Barcode Segments at Room Temperature. Nano Letters, 2017, 17, 2652-2659.	4.5	20
54	Absorption and transmission of light in IIIâ€“V nanowire arrays for tandem solar cell applications. Nanotechnology, 2017, 28, 205203.	1.3	34

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55	Growth and optical properties of In x Ga1â^'x P nanowires synthesized by selective-area epitaxy. Nano Research, 2017, 10, 672-682.	5.8	24
56	Towards high efficiency nanowire solar cells. Nano Today, 2017, 12, 31-45.	6.2	153
57	Room-temperature InP/InAsP Quantum Discs-in-Nanowire Infrared Photodetectors. Nano Letters, 2017, 17, 3356-3362.	4.5	36
58	Optimization of Current Injection in AlGaInP Coreâ^'Shell Nanowire Light-Emitting Diodes. Nano Letters, 2017, 17, 3599-3606.	4.5	15
59	Bending and Twisting Lattice Tilt in Strained Coreâ€“Shell Nanowires Revealed by Nanofocused X-ray Diffraction. Nano Letters, 2017, 17, 4143-4150.	4.5	43
60	Radial tunnel diodes based on InP/InGaAs core-shell nanowires. Applied Physics Letters, 2017, 110, .	1.5	7
61	In_xGa_{1â€“x}P Nanowire Growth Dynamics Strongly Affected by Doping Using Diethylzinc. Nano Letters, 2017, 17, 702-707.	4.5	28
62	Growth of wurtzite Al_xGa_{1â^'x}P nanowire shells and characterization by Raman spectroscopy. Nanotechnology, 2017, 28, 035706.	1.3	6
63	Defect-induced infrared electroluminescence from radial GaInP/AlGaInP quantum well nanowire array light- emitting diodes. Nanotechnology, 2017, 28, 485205.	1.3	6
64	InP/InAsP Nanowire-Based Spatially Separate Absorption and Multiplication Avalanche Photodetectors. ACS Photonics, 2017, 4, 2693-2698.	3.2	27
65	Cellular traction forces: a useful parameter in cancer research. Nanoscale, 2017, 9, 19039-19044.	2.8	54
66	Anti-Stokes photoluminescence probing k-conservation and thermalization of minority carriers in degenerately doped semiconductors. Nature Communications, 2017, 8, 1634.	5.8	6
67	Time-resolved photoluminescence characterization of GaAs nanowire arrays on native substrate. Nanotechnology, 2017, 28, 505706.	1.3	7
68	Carrier Recombination Processes in Gallium Indium Phosphide Nanowires. Nano Letters, 2017, 17, 4248-4254.	4.5	20
69	GaAsP Nanowire Solar Cell Development Towards Nanowire/Si Tandem Applications. , 2017, , .		0
70	Growth and optimization of GaInP/InP nanowire tunnel diode. , 2017, , .		1
71	Bragg coherent x-ray diffractive imaging of a single indium phosphide nanowire. Journal of Optics (United Kingdom), 2016, 18, 064007.	1.0	30
72	Translocation of 40â€‰nm diameter nanowires through the intestinal epithelium of Daphnia magna. Nanotoxicology, 2016, 10, 1160-1167.	1.6	34

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73	Doping evaluation of InP nanowires for tandem junction solar cells. Nanotechnology, 2016, 27, 065706.	1.3	15
74	Strategies to obtain pattern fidelity in nanowire growth from large-area surfaces patterned using nanoimprint lithography. Nano Research, 2016, 9, 2852-2861.	5.8	56
75	Confinement effects on Brillouin scattering in semiconductor nanowire photonic crystal. Physical Review B, 2016, 94, .	1.1	7
76	InP nanowire p-type doping via Zinc indiffusion. Journal of Crystal Growth, 2016, 451, 18-26.	0.7	5
77	Radial Nanowire Light-Emitting Diodes in the (Al_xGa_{1â€“x})_yIn_{1â€“y}P Material System. Nano Letters, 2016, 16, 656-662.	4.5	37
78	Comparing Hall Effect and Field Effect Measurements on the Same Single Nanowire. Nano Letters, 2016, 16, 205-211.	4.5	35
79	Growth parameter design for homogeneous material composition in ternary Ga_xIn_{1â^’x}P nanowires. Nanotechnology, 2015, 26, 435601.	1.3	19
80	Doping GaP Coreâ€“Shell Nanowire pnâ€Junctions: A Study by Offâ€Axis Electron Holography. Small, 2015, 11, 2687-2695.	5.2	22
81	A Comparative Study of Absorption in Vertically and Laterally Oriented InP Coreâ€“Shell Nanowire Photovoltaic Devices. Nano Letters, 2015, 15, 1809-1814.	4.5	57
82	Study of carrier concentration in single InP nanowires by luminescence and Hall measurements. Nanotechnology, 2015, 26, 045705.	1.3	38
83	Structural Properties of Wurtzite InPâ€“InGaAs Nanowire Coreâ€“Shell Heterostructures. Nano Letters, 2015, 15, 2462-2467.	4.5	31
84	In Situ Characterization of Nanowire Dimensions and Growth Dynamics by Optical Reflectance. Nano Letters, 2015, 15, 3597-3602.	4.5	53
85	Carrier Recombination Dynamics in Sulfur-Doped InP Nanowires. Nano Letters, 2015, 15, 7238-7244.	4.5	26
86	Photon upconversion in degenerately sulfur doped InP nanowires. Nanoscale, 2015, 7, 20503-20509.	2.8	1
87	IIIâ€“V Nanowire Synthesis by Use of Electrodeposited Gold Particles. Nano Letters, 2015, 15, 134-138.	4.5	22
88	Bulk-like transverse electron mobility in an array of heavily<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math>-doped InP nanowires probed by terahertz spectroscopy. Physical Review B, 2014, 90, .	1.1	24
89	FIB Plan and Side View Cross-Sectional TEM Sample Preparation of Nanostructures. Microscopy and Microanalysis, 2014, 20, 133-140.	0.2	23
90	In situetching for control over axial and radial III-V nanowire growth rates using HBr. Nanotechnology, 2014, 25, 505601.	1.3	10

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91	Semiconductor nanostructures enabled by aerosol technology. Frontiers of Physics, 2014, 9, 398-418.	2.4	19
92	Synthesis of Doped InP Coreâ€“Shell Nanowires Evaluated Using Hall Effect Measurements. Nano Letters, 2014, 14, 749-753.	4.5	30
93	Absorption of light in InP nanowire arrays. Nano Research, 2014, 7, 816-823.	5.8	85
94	Growth and characterization of wurtzite GaP nanowires with control over axial and radial growth by use of HCl in-situ etching. Journal of Crystal Growth, 2014, 386, 47-51.	0.7	32
95	Study of photocurrent generation in InP nanowire-based p+-i-n+ photodetectors. Nano Research, 2014, 7, 544-552.	5.8	37
96	Au-Seeded Growth of Vertical and in-Plane IIIâ€“V Nanowires on Graphite Substrates. Nano Letters, 2014, 14, 1707-1713.	4.5	41
97	Inherently Fluorescent Nanowires for Cellular Mechanosensing. Biophysical Journal, 2014, 106, 812a.	0.2	0
98	InN quantum dots on GaN nanowires grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 421-424.	0.8	4
99	Evaluation of Doping in GaP Core-Shell Nanowire pn Junction by Off-Axis Electron Holography. Microscopy and Microanalysis, 2014, 20, 288-289.	0.2	2
100	Large-energy-shift photon upconversion in degenerately doped InP nanowires by direct excitation into the electron gas. Nano Research, 2013, 6, 752-757.	5.8	6
101	Fluorescent Nanowire Heterostructures as a Versatile Tool for Biology Applications. Nano Letters, 2013, 13, 4728-4732.	4.5	43
102	Photoluminescence study of Zn-doped wurtzite InP core-shell nanowires. Applied Physics Letters, 2013, 102, 032105.	1.5	3
103	Semiconductor-Oxide Heterostructured Nanowires Using Postgrowth Oxidation. Nano Letters, 2013, 13, 5961-5966.	4.5	8
104	InP Nanowire Array Solar Cells Achieving 13.8% Efficiency by Exceeding the Ray Optics Limit. Science, 2013, 339, 1057-1060.	6.0	1,093
105	Structural investigation of GaInP nanowires using X-ray diffraction. Thin Solid Films, 2013, 543, 100-105.	0.8	15
106	Optical Far-Field Method with Subwavelength Accuracy for the Determination of Nanostructure Dimensions in Large-Area Samples. Nano Letters, 2013, 13, 2662-2667.	4.5	15
107	Photoluminescence study of as-grown vertically standing wurtzite InP nanowire ensembles. Nanotechnology, 2013, 24, 115706.	1.3	15
108	Currentâ€“Voltage Characterization of Individual As-Grown Nanowires Using a Scanning Tunneling Microscope. Nano Letters, 2013, 13, 5182-5189.	4.5	16

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109	Solidâ€“liquidâ€“vapor metal-catalyzed etching of lateral and vertical nanopores. Nanotechnology, 2013, 24, 415303.	1.3	4
110	Reflection measurements to reveal the absorption in nanowire arrays. Optics Letters, 2013, 38, 1449.	1.7	11
111	Transparently wrap-gated semiconductor nanowire arrays for studies of gate-controlled photoluminescence. , 2013, , .		1
112	Optical characterization of InAs quantum wells and dots grown radially on wurtzite InP nanowires. Nanotechnology, 2013, 24, 225203.	1.3	11
113	A luminescence study of doping effects in InP-based radial nanowire structures. Journal of Physics: Conference Series, 2013, 471, 012040.	0.3	0
114	Single GaInP nanowire p-i-n junctions near the direct to indirect bandgap crossover point. Applied Physics Letters, 2012, 100, 251103.	1.5	13
115	High-Performance InAs Nanowire MOSFETs. IEEE Electron Device Letters, 2012, 33, 791-793.	2.2	60
116	Electron Trapping in InP Nanowire FETs with Stacking Faults. Nano Letters, 2012, 12, 151-155.	4.5	102
117	Tunnel Field-Effect Transistors Based on InP-GaAs Heterostructure Nanowires. ACS Nano, 2012, 6, 3109-3113.	7.3	89
118	Surface Chemistry, Structure, and Electronic Properties from Microns to the Atomic Scale of Axially Doped Semiconductor Nanowires. ACS Nano, 2012, 6, 9679-9689.	7.3	37
119	Electrical and optical properties of InP nanowire ensemble p⁺â€“iâ€“n⁺photodetectors. Nanotechnology, 2012, 23, 135201.	1.3	31
120	Particle-assisted Ga_xIn_{1â^'x}P nanowire growth for designed bandgap structures. Nanotechnology, 2012, 23, 245601.	1.3	48
121	15 nm diameter InAs nanowire MOSFETs. , 2011, , .		0
122	Gate-Induced Fermi Level Tuning in InP Nanowires at Efficiency Close to the Thermal Limit. Nano Letters, 2011, 11, 1127-1130.	4.5	19
123	Probing the Wurtzite Conduction Band Structure Using State Filling in Highly Doped InP Nanowires. Nano Letters, 2011, 11, 2286-2290.	4.5	66
124	Unit cell parameters of wurtzite InP nanowires determined by x-ray diffraction. Nanotechnology, 2011, 22, 425704.	1.3	49
125	A New Route toward Semiconductor Nanospintronics: Highly Mn-Doped GaAs Nanowires Realized by Ion-Implantation under Dynamic Annealing Conditions. Nano Letters, 2011, 11, 3935-3940.	4.5	47
126	Axial InP Nanowire Tandem Junction Grown on a Silicon Substrate. Nano Letters, 2011, 11, 2028-2031.	4.5	114

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127	Growth of doped InAsyP1â^'y nanowires with InP shells. Journal of Crystal Growth, 2011, 331, 8-14.	0.7	27
128	Electron Image Series Reconstruction of Twin Interfaces in InP Superlattice Nanowires. Microscopy and Microanalysis, 2011, 17, 752-758.	0.2	4
129	Photovoltaics with piezoelectric core-shell nanowires. AIP Conference Proceedings, 2011, , .	0.3	2
130	Dual-gate induced InP nanowire diode. , 2011, , .		0
131	Nanowires With Promise for Photovoltaics. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1050-1061.	1.9	123
132	Dynamics of extremely anisotropic etching of InP nanowires by HCl. Chemical Physics Letters, 2011, 502, 222-224.	1.2	16
133	Valence band splitting in wurtzite InP nanowires observed by photoluminescence and photoluminescence excitation spectroscopy. Nano Research, 2011, 4, 159-163.	5.8	41
134	Temperature and frequency characterization of InAs nanowire and HfO2 interface using capacitanceâ€“voltage method. Microelectronic Engineering, 2011, 88, 444-447.	1.1	2
135	Fabrication and characterization of AlP-GaP core-shell nanowires. Journal of Crystal Growth, 2011, 324, 290-295.	0.7	6
136	Doping profile of InP nanowires directly imaged by photoemission electron microscopy. Applied Physics Letters, 2011, 99, 233113.	1.5	16
137	InAs quantum dots and quantum wells grown on stacking-fault controlled InP nanowires with wurtzite crystal structure. Applied Physics Letters, 2011, 99, 131915.	1.5	30
138	Degenerate p-doping of InP nanowires for large area tunnel diodes. Applied Physics Letters, 2011, 99, .	1.5	28
139	Doping of semiconductor nanowires. Journal of Materials Research, 2011, 26, 2142-2156.	1.2	139
140	In situ etching for total control over axial and radial nanowire growth. Nano Research, 2010, 3, 264-270.	5.8	135
141	Time-resolved photoluminescence investigations on HfO₂-capped InP nanowires. Nanotechnology, 2010, 21, 105711.	1.3	18
142	Integration, gap formation, and sharpening of III-V heterostructure nanowires by selective etching. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 21-26.	0.6	12
143	Bias-controlled friction of InAs nanowires on a silicon nitride layer studied by atomic force microscopy. Physical Review B, 2010, 82, .	1.1	16
144	Doping Incorporation in InAs nanowires characterized by capacitance measurements. Journal of Applied Physics, 2010, 108, .	1.1	40

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145	Changes in Contact Angle of Seed Particle Correlated with Increased Zincblende Formation in Doped InP Nanowires. Nano Letters, 2010, 10, 4807-4812.	4.5	83
146	Probing Strain in Bent Semiconductor Nanowires with Raman Spectroscopy. Nano Letters, 2010, 10, 1280-1286.	4.5	85
147	High-Performance Single Nanowire Tunnel Diodes. Nano Letters, 2010, 10, 974-979.	4.5	77
148	The electrical and structural properties of n-type InAs nanowires grown from metalâ€“organic precursors. Nanotechnology, 2010, 21, 205703.	1.3	86
149	Periodic nanowire structures. , 2010, , .		0
150	Diameter-dependent conductance of InAs nanowires. Journal of Applied Physics, 2009, 106, .	1.1	77
151	Determination of the wurtzite content and orientation distribution of nanowire ensembles. Materials Research Society Symposia Proceedings, 2009, 1206, 113901.	0.1	0
152	Preferential Interface Nucleation: An Expansion of the VLS Growth Mechanism for Nanowires. Advanced Materials, 2009, 21, 153-165.	11.1	309
153	Orientationâ€Dependent Opticalâ€Polarization Properties of Single Quantum Dots in Nanowires. Small, 2009, 5, 2134-2138.	5.2	33
154	Zinc Incorporation via the Vaporâ^'Liquidâ^'Solid Mechanism into InP Nanowires. Journal of the American Chemical Society, 2009, 131, 4578-4579.	6.6	41
155	Epitaxial Growth of Aligned Semiconductor Nanowire Metamaterials for Photonic Applications. Advanced Functional Materials, 2008, 18, 1039-1046.	7.8	56
156	Tunable double quantum dots in InAs nanowires. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1202-1204.	1.3	8
157	Twinning superlattices in indium phosphide nanowires. Nature, 2008, 456, 369-372.	13.7	625
158	Precursor evaluation forin situInP nanowire doping. Nanotechnology, 2008, 19, 445602.	1.3	92
159	Local and anisotropic excitation of surface plasmon polaritons by semiconductor nanowires. Optics Express, 2008, 16, 5013.	1.7	9
160	Epitaxial Growth of III-V Nanowires on Group IV Substrates. Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	8
161	Optical Anisotropy of Semiconductor Nanowires. , 2008, , 127-145.		5
162	Epitaxial Growth of III-V Nanowires on Group IV Substrates. MRS Bulletin, 2007, 32, 117-122.	1.7	95

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163	Tunable few-electron quantum dots in InAs nanowires. Nanotechnology, 2007, 18, 044014.	1.3	31
164	Modification of the photoluminescence anisotropy of semiconductor nanowires by coupling to surface plasmon polaritons. Optics Letters, 2007, 32, 2097.	1.7	8
165	Towards vertical III-V nanowire devices on silicon. Device Research Conference, IEEE Annual, 2007, , .	0.0	1
166	Towards vertical III-V nanowire devices. , 2007, , .		0
167	Three-Dimensional Morphology of GaPâ^'GaAs Nanowires Revealed by Transmission Electron Microscopy Tomography. Nano Letters, 2007, 7, 3051-3055.	4.5	87
168	Synergetic nanowire growth. Nature Nanotechnology, 2007, 2, 541-544.	15.6	220
169	Remote p-Doping of InAs Nanowires. Nano Letters, 2007, 7, 1144-1148.	4.5	70
170	Single Quantum Dot Nanowire LEDs. Nano Letters, 2007, 7, 367-371.	4.5	349
171	Growth Kinetics of Heterostructured GaPâ^'GaAs Nanowires. Journal of the American Chemical Society, 2006, 128, 1353-1359.	6.6	182
172	Giant optical birefringence in ensembles of semiconductor nanowires. Applied Physics Letters, 2006, 89, 233117.	1.5	66
173	Fabrication of Semiconductor Nanowires for Electronic Transport Measurements. Chimia, 2006, 60, 729-734.	0.3	21
174	Interface study on heterostructured GaPâ€“GaAs nanowires. Nanotechnology, 2006, 17, 4010-4013.	1.3	60
175	Epitaxial III-V Nanowires on Silicon for Vertical Devices. ECS Transactions, 2006, 3, 415-423.	0.3	1
176	Enhancement of the electroabsorption in multiple quantum well structures containing a nipi delta-doping superlattice. Applied Physics Letters, 2005, 86, 023501.	1.5	1
177	Optically Bright Quantum Dots in Single Nanowires. Nano Letters, 2005, 5, 1439-1443.	4.5	266
178	Defect-free InP nanowires grown in [001] direction on InP (001). Applied Physics Letters, 2004, 85, 2077-2079.	1.5	173
179	Direct imaging of the atomic structure inside a nanowire by scanning tunnelling microscopy. Nature Materials, 2004, 3, 519-523.	13.3	79
180	Size- and shape-controlled GaAs nano-whiskers grown by MOVPE: a growth study. Journal of Crystal Growth, 2004, 260, 18-22.	0.7	112

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181	Growth of one-dimensional nanostructures in MOVPE. Journal of Crystal Growth, 2004, 272, 211-220.	0.7	278
182	Semiconductor nanowires for 0D and 1D physics and applications. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 25, 313-318.	1.3	172
183	Nanowire Arrays Defined by Nanoimprint Lithography. Nano Letters, 2004, 4, 699-702.	4.5	383
184	Site control of InAs quantum dots on a patterned InP surface: As/P exchange reactions. Journal of Crystal Growth, 2003, 248, 310-316.	0.7	0
185	InAs quantum dots grown on InAlGaAs lattice matched to InP. Journal of Crystal Growth, 2003, 252, 481-485.	0.7	20
186	Fabrication of individually seeded nanowire arrays by vapourâ€“liquidâ€“solid growth. Nanotechnology, 2003, 14, 1255-1258.	1.3	189
187	Transport through an isolated artificial molecule formed from stacked self-assembled quantum dots. Applied Physics Letters, 2003, 82, 2655-2657.	1.5	23
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